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AND

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AND

AND

mosfet

AND

AND

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1. ☐ **Effect of aspect ratio on forward voltage drop in trench insulated gate bipolar transistor • ARTICLE**
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Jin-Woo Moon, Yearn-Ik Choi and Sang-Koo Chung
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3. ☐ **High-voltage lateral trench gate SOI-LDMOSFETs • ARTICLE**
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